



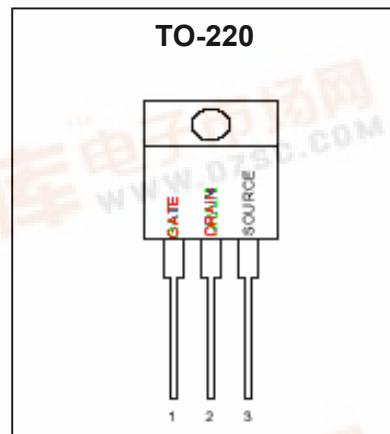
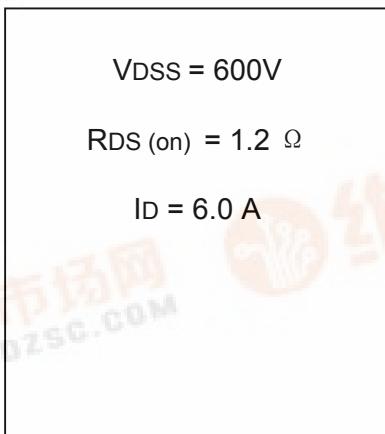
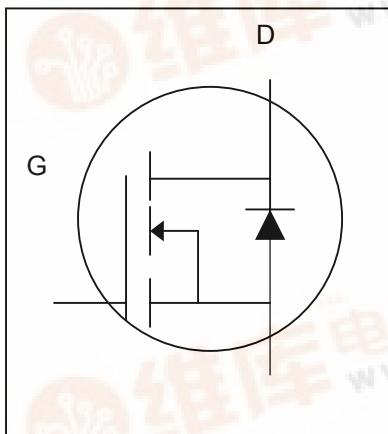
B06N60

N-Channel Power MOSFET

- Advanced Process Technology
- Ultra low On-Resistance Provides Higher Efficiency
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- IDSS and VDS (on) Specified at Elevated Temperature

## DESCRIPTION

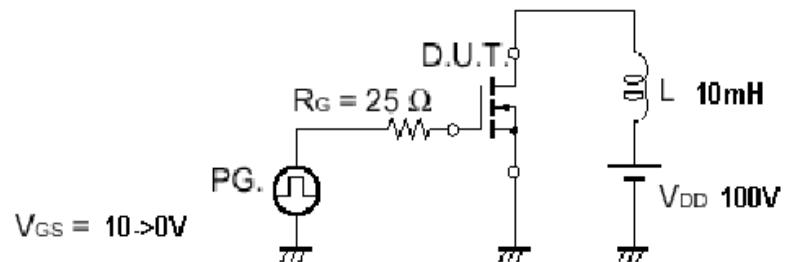
This high voltage MOSFET used an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation time. Designed for high voltage, high speed switching application in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operation areas critical and offer additional and safety margin against unexpected voltage transients.



## ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain to Current – Continuous	$I_D$	6.0	A
Gate-to-Source Voltage – Continue - Non-repetitive	$V_{GS}$ $V_{GSM}$	$+/ - 20$ $+/ - 40$	V
Total Power Dissipation Derate Above 25°C	$PD$	125 1.0	W W/°C
Operating and Storage Temperature Range	$T_{J, T_{STG}}$	-55 to 150	°C
Single Pulse Drain-to-Source Avalanche Energy – $T_J = 25^{\circ}C$ ( $V_{DD} = 100V$ , $V_{GS} = 10V$ , $I_L = 6A$ , $L = 10mH$ , $R_G = 25\Omega$ )	$E_{AS}$	180	mJ
Thermal Resistance – Junction to Case - Junction to Ambient	$\theta_{JC}$ $\theta_{JA}$	1.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purpose, 1/8" from case for 10 seconds	$T_L$	260	°C

## TEST CIRCUIT



Test Circuit – Avalanche Capability



**B06N60**  
**N-Channel Power MOSFET**

## ELECTRICAL CHARACTERISTICS

Unless otherwise specified,  $T_J = 25^\circ\text{C}$ .

Characteristic		Symbol	B06N60		
Characteristic	Symbol	Min	Typ	Max	Units
Drain-Source Breakdown Voltage ( $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$ )	$V_{(BR)DSS}$	600			V
Drain-Source Leakage Current ( $V_{DS} = 600\text{ V}$ , $V_{GS} = 0\text{ V}$ ) ( $V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$ )	$I_{DSS}$			100 50	$\mu\text{A}$
Gate-Source Leakage Current-Forward ( $V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$ )	$I_{GSSF}$			100	nA
Gate-Source Leakage Current-Reverse ( $V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$ )	$I_{GSSR}$			100	nA
Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$ )	$V_{GS(\text{th})}$	2.0		4.0	V
Static Drain-Source On-Resistance ( $V_{GS} = 10\text{ V}$ , $I_D = 3.5\text{A}$ ) *	$R_{DS(\text{on})}$			1.2	$\Omega$
Forward Transconductance ( $V_{DS} = 15\text{ V}$ , $I_D = 3.0\text{A}$ ) *	$g_{FS}$	3.4			mhos
Input Capacitance	$C_{iss}$		1498	2100	pF
Output Capacitance	$C_{oss}$		158	220	pF
Reverse Transfer Capacitance	$C_{rss}$		29	60	pF
Turn-On Delay Time	$t_{d(on)}$		14	30	ns
Rise Time	$t_r$		19	40	ns
Turn-Off Delay Time	$t_{d(off)}$		40	80	ns
Fall Time	$t_f$		26	55	ns
Total Gate Charge	$Q_g$		35.5	50	nC
Gate-Source Charge	$Q_{gs}$		8.1		nC
Gate-Drain Charge	$Q_{gd}$		14.1		nC
Internal Drain Inductance (Measured from the drain lead 0.25" from package to center of die)	$L_D$		4.5		nH
Internal Drain Inductance (Measured from the source lead 0.25" from package to source bond pad)	$L_S$		7.5		nH
SOURCE-DRAIN DIODE CHARACTERISTICS					
Forward On-Voltage(1)	$(I_S = 6.0\text{ A},$ $d_{IS}/dt = 100\text{A}/\mu\text{s})$	$V_{SD}$		0.83	V
Forward Turn-On Time		$t_{on}$		**	ns
Reverse Recovery Time		$t_{rr}$		266	ns

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

\*\* Negligible, Dominated by circuit inductance

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## TYPICAL ELECTRICAL CHARACTERISTICS

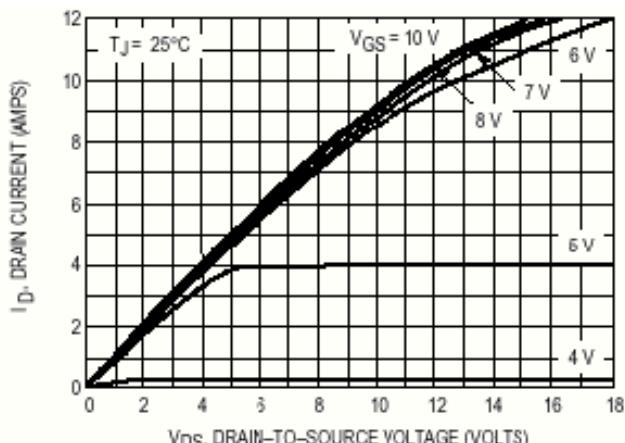


Figure 1. On-Region Characteristics

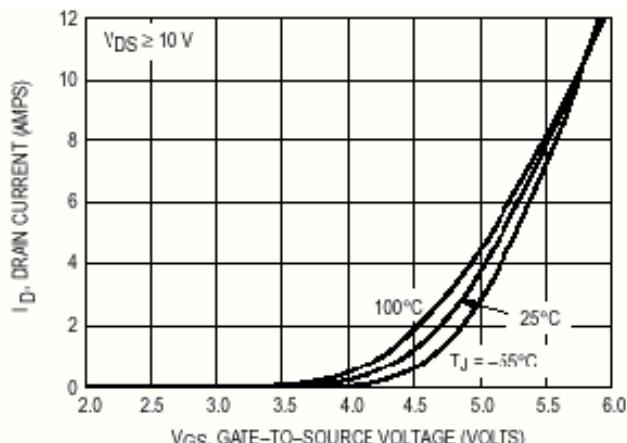


Figure 2. Transfer Characteristics

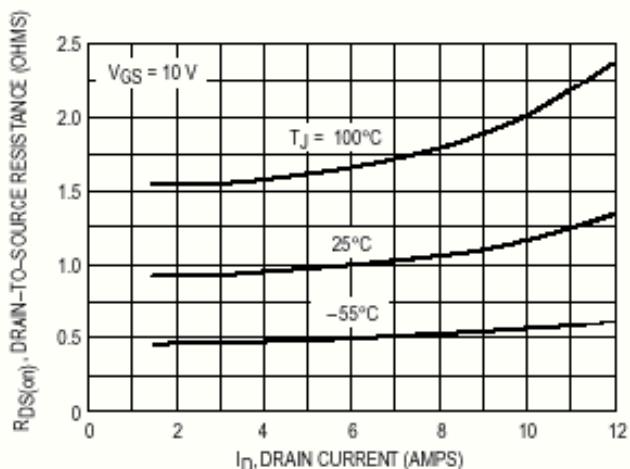


Figure 3. On-Resistance versus Drain Current and Temperature

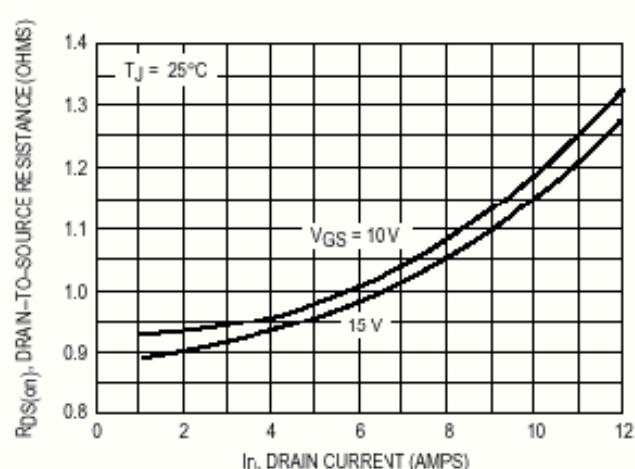


Figure 4. On-Resistance versus Drain Current and Gate Voltage

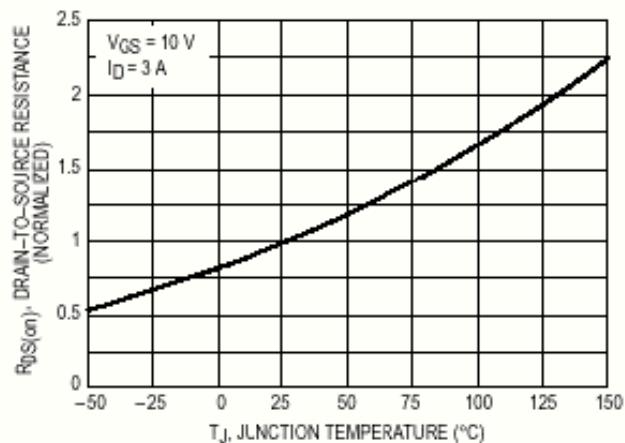


Figure 5. Cn-Resistance Variation with Temperature

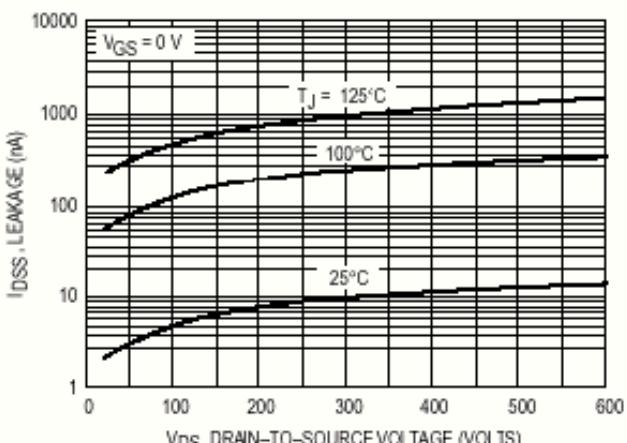


Figure 6. Drain-To-Source Leakage Current versus Voltage

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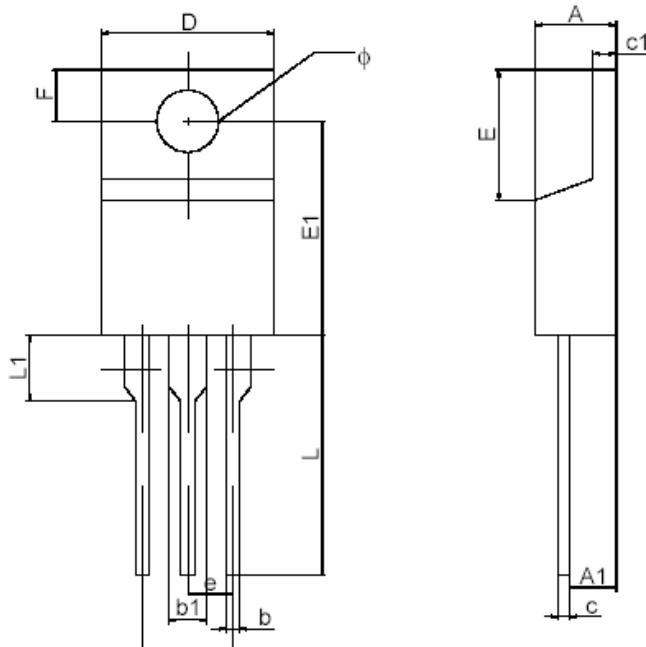
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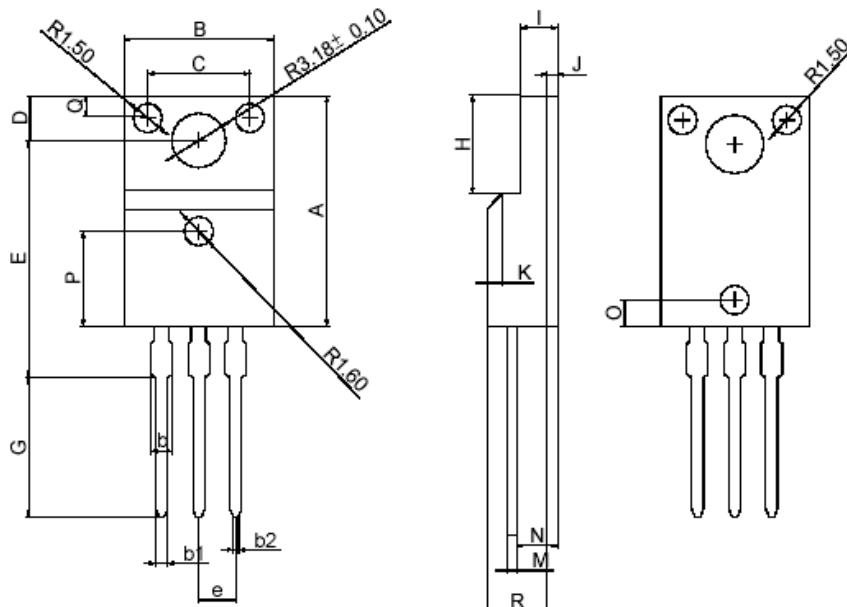
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**PACKAGE DIMENSION**
**TO-220**

**PIN 1: GATE**  
**PIN 2: DRAIN**  
**PIN 3: SOURCE**

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.47	—	4.67	0.174	—	0.184
A1	8.68	—	8.88	0.340	—	0.351
b	0.76	—	0.81	0.030	—	0.032
b1	1.17	—	1.37	0.045	—	0.054
c	0.31	—	0.33	0.012	—	0.021
c1	1.17	—	1.37	0.044	—	0.054
D	10.01	—	10.11	0.394	—	0.406
E	8.60	—	8.80	0.335	—	0.350
E1	12.08	—	12.48	0.475	—	0.491
e	—	2.54	—	—	0.100	—
e1	4.58	—	5.18	0.186	—	0.204
F	8.69	—	8.89	0.342	—	0.354
L	13.40	—	13.60	0.532	—	0.549
L1	9.68	—	9.88	0.384	—	0.186
Φ	3.79	—	3.89	0.148	—	0.163

Side View

Front View

**TO-220FP**


Front View

Side View

Back View

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	15.87	—	16.07	0.621	—	0.628
B	9.95	—	10.06	0.392	—	0.406
C	—	7.00	—	—	0.275	—
D	3.80	—	3.90	0.153	—	0.154
E	15.00	—	15.00	0.591	—	0.590
G	9.45	—	10.06	0.372	—	0.398
H	5.45	—	5.66	0.219	—	0.270
I	8.34	—	8.74	0.332	—	0.338
J	—	0.70	—	—	0.028	—
K	—	1.00	—	—	0.039	—
M	9.45	—	9.60	0.375	—	0.394
N	8.68	—	9.06	0.341	—	0.347
O	—	1.00	—	—	0.039	—
P	—	0.50	—	—	0.020	—
Q	—	1.00	—	—	0.039	—
R	4.50	—	4.60	0.177	—	0.185
b	—	1.47	—	—	0.058	—
b1	9.70	—	9.90	0.382	—	0.398
b2	9.26	—	9.46	0.360	—	0.376
e	—	0.54	—	—	0.020	—

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